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(54) **SEMICONDUCTOR DEVICE WITH
SELF-ALIGNED WAVY CONTACT PROFILE
AND METHOD OF FORMING THE SAME**

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ABSTRACT

A semiconductor device and method of manufacturing the semiconductor device are provided. An exemplary semiconductor device comprises a fin disposed over a substrate, wherein the fin includes a channel region and a source/drain region; a gate structure disposed over the substrate and over the channel region of the fin; a source/drain feature epitaxially grown in the source/drain region of the fin, wherein the source/drain feature includes a top epitaxial layer and a lower epitaxial layer formed below the top epitaxial layer, and the lower epitaxial layer includes a wavy top surface; and a contact having a wavy bottom surface matingly engaged with the wavy top surface of the lower epitaxial layer of the source/drain feature.